

MOSFET - Power, Single N-Channel, DFN5/DFNW5 40 V, 1.7 mΩ, 185 A

NVMFS5C430N

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS5C430NWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V _{DSS}	40	V
Gate-to-Source Voltage		V _{GS}	±20	V
Continuous Drain Current $R_{θJC}$ (Notes 1, 3)	Steady State	T _C = 25°C	I _D	185
		T _C = 100°C		131
Power Dissipation $R_{θJC}$ (Note 1)		T _C = 25°C	P _D	106
		T _C = 100°C		53
Continuous Drain Current $R_{θJA}$ (Notes 1, 2, 3)	Steady State	T _A = 25°C	I _D	35
		T _A = 100°C		25
Power Dissipation $R_{θJA}$ (Notes 1 & 2)		T _A = 25°C	P _D	3.8
		T _A = 100°C		1.9
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs	I _{DM}	900	A
Operating Junction and Storage Temperature		T _J , T _{stg}	-55 to + 175	°C
Source Current (Body Diode)		I _S	102	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 15 A)		E _{AS}	338	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C

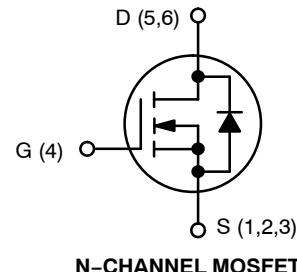
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	R _{θJC}	1.4	°C/W
Junction-to-Ambient – Steady State (Note 2)	R _{θJA}	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

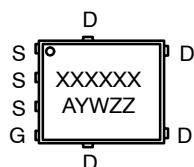
V _{(BR)DSS}	R _{DS(ON) MAX}	I _{D MAX}
40 V	1.7 mΩ @ 10 V	185 A



DFN5 (SO-8FL)
CASE 488AA

DFNW5
(FULL-CUT SO8FL WF)
CASE 507BA

MARKING DIAGRAM



XXXXXX = 5C430N
(NVMFS5C430N) or
430NWF
(NVMFS5C430NWF)

A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFS5C430N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$		40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$				12.8		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}$, $V_{\text{DS}} = 40 \text{ V}$	$T_J = 25^\circ\text{C}$		10		μA
			$T_J = 125^\circ\text{C}$			100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}$, $V_{\text{GS}} = 20 \text{ V}$				100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}$, $I_D = 250 \mu\text{A}$		2.5		3.5	V
Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$				-8.2		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 50 \text{ A}$		1.4	1.7	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 15 \text{ V}$, $I_D = 50 \text{ A}$			130		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$, $V_{\text{DS}} = 25 \text{ V}$		3300		pF
Output Capacitance	C_{oss}			1600		
Reverse Transfer Capacitance	C_{rss}			45		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 20 \text{ V}$; $I_D = 50 \text{ A}$		47		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			10		
Gate-to-Source Charge	Q_{GS}			16		
Gate-to-Drain Charge	Q_{GD}			7		
Plateau Voltage	V_{GP}			4.7		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 20 \text{ V}$, $I_D = 50 \text{ A}$, $R_G = 2.5 \Omega$		13		ns
Rise Time	t_r			48		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			29		
Fall Time	t_f			8		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}$, $I_S = 50 \text{ A}$	$T_J = 25^\circ\text{C}$		0.83	1.2	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0 \text{ V}$, $dI_S/dt = 100 \text{ A}/\mu\text{s}$, $I_S = 50 \text{ A}$			57		ns
Charge Time	t_a				30		
Discharge Time	t_b				27		
Reverse Recovery Charge	Q_{RR}				68		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

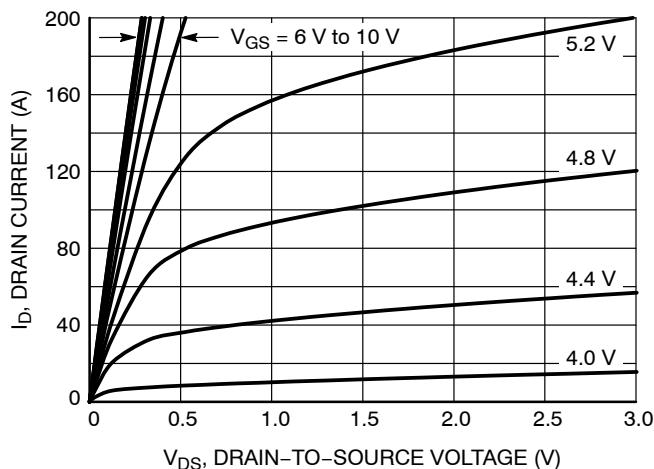


Figure 1. On-Region Characteristics

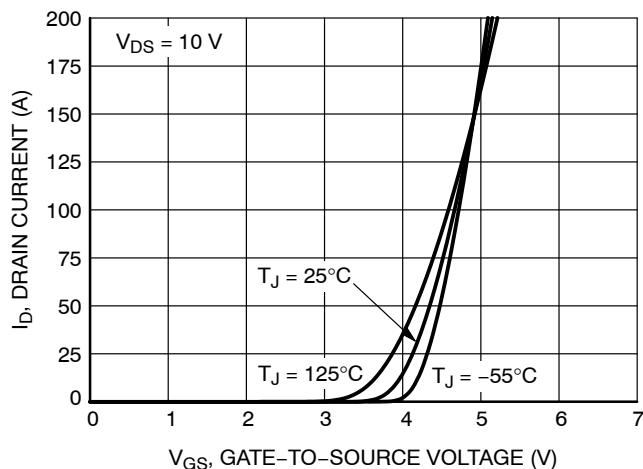


Figure 2. Transfer Characteristics

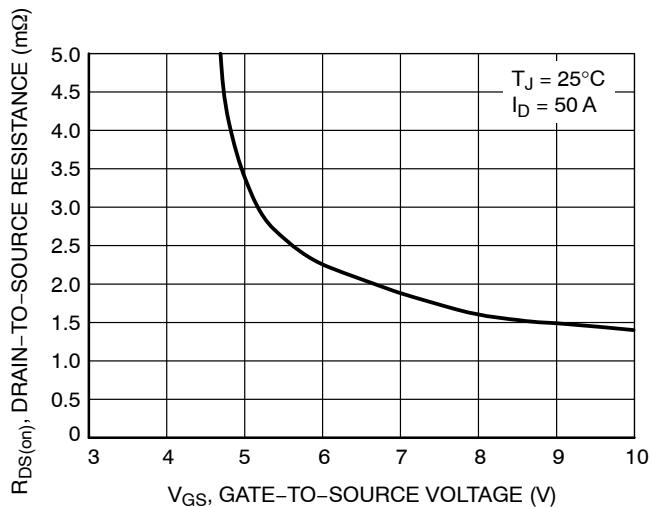


Figure 3. On-Resistance vs. Gate-to-Source Voltage

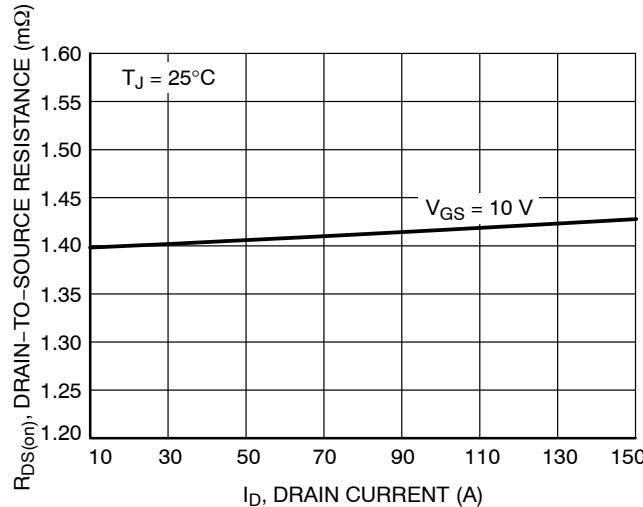


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

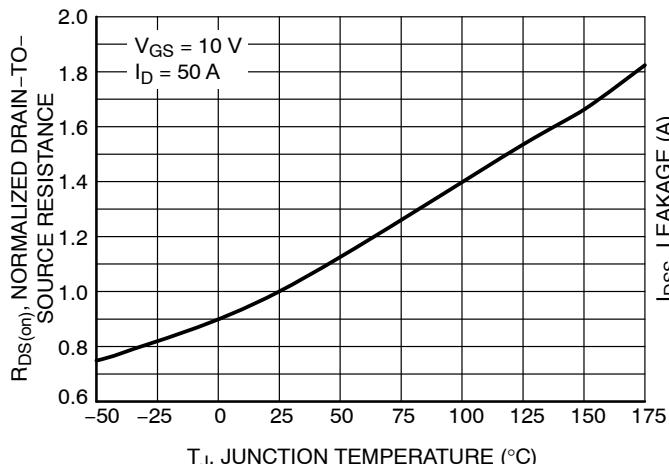


Figure 5. On-Resistance Variation with Temperature

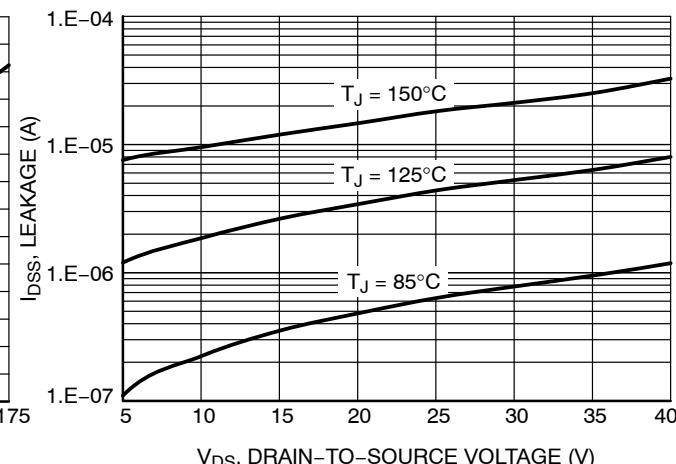
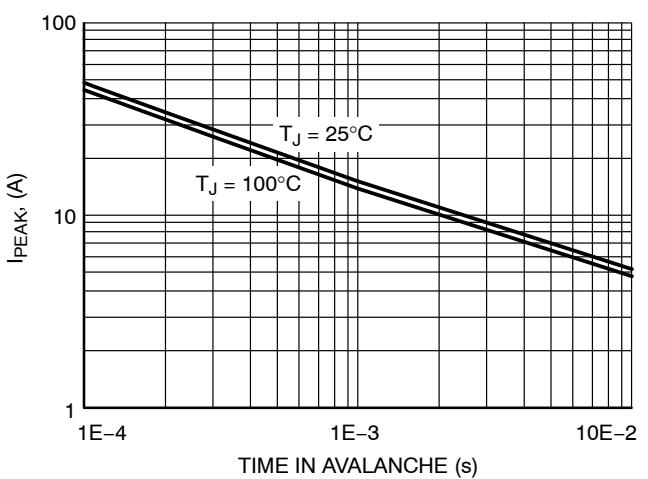
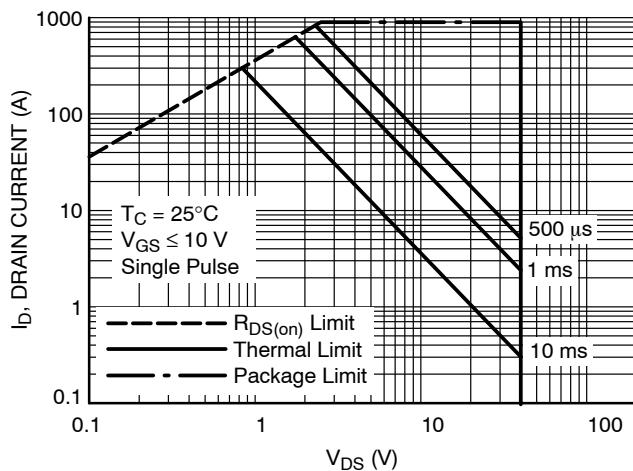
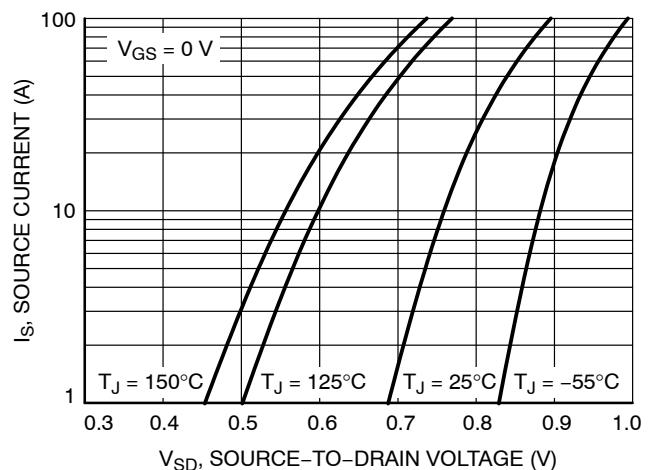
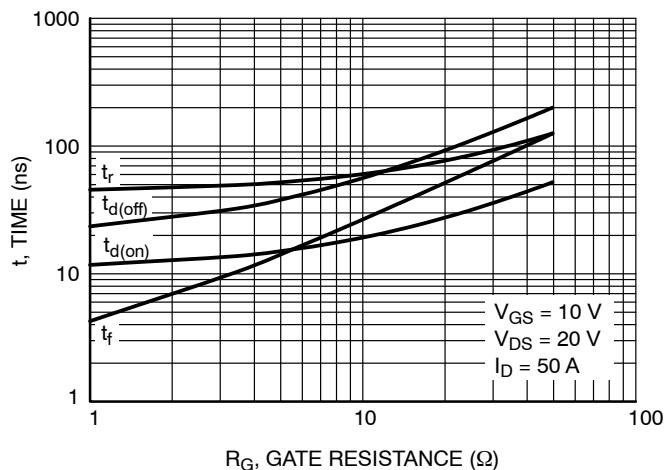
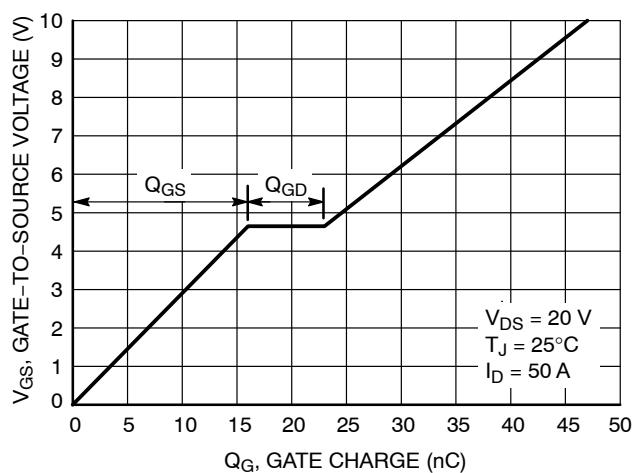
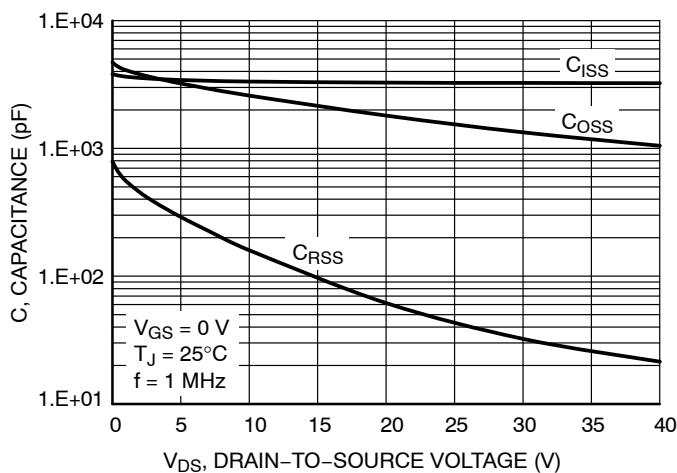
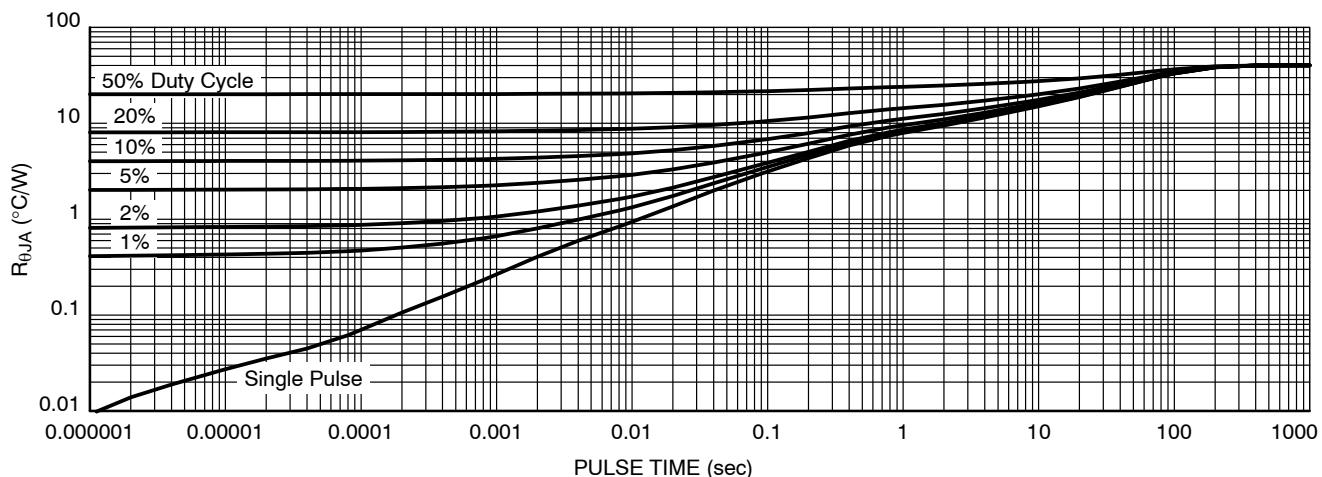


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS**Figure 13. Thermal Characteristics****DEVICE ORDERING INFORMATION**

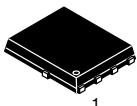
Device	Marking	Package	Shipping [†]
NVMFS5C430NT1G	5C430N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C430NWFT1G	430NWF	DFNW5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS5C430NT3G	5C430N	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5C430NWFT3G	430NWF	DFNW5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel
NVMFS5C430NAFT1G	5C430	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C430NAFT1G-YE	5C430	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C430NWFAFT1G	430NWF	DFNW5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS5C430NWFT1G	430NWF	DFNW5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemiTM



SCALE 2:1

**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N**

DATE 25 JUN 2018

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
n	0 °		12 °

GENERIC MARKING DIAGRAM*



xxxxxx = Specific Device Code

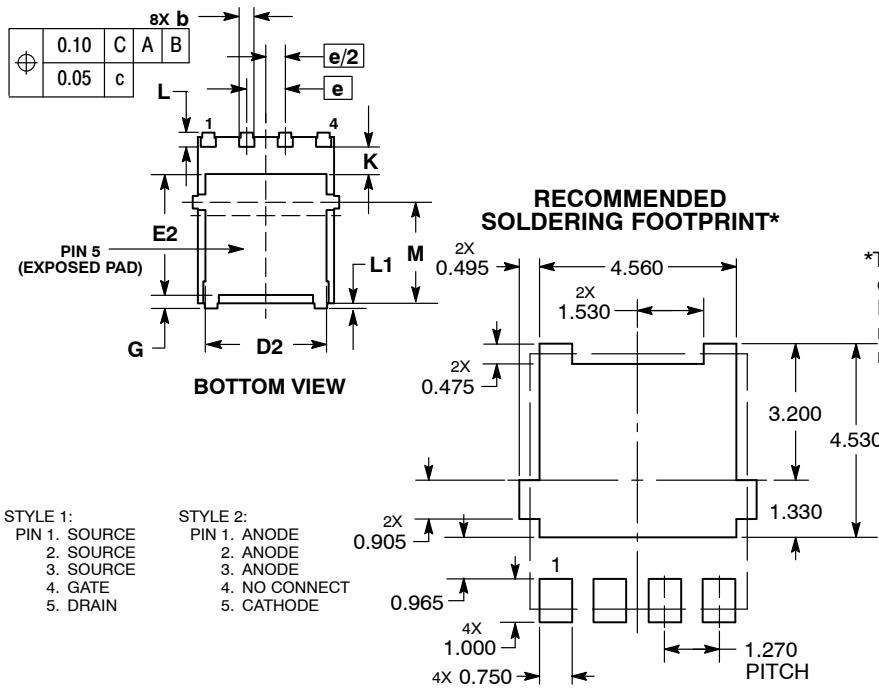
A = Assembly Location

Y = Year

W = Work Week

ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

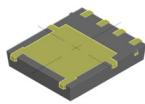
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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

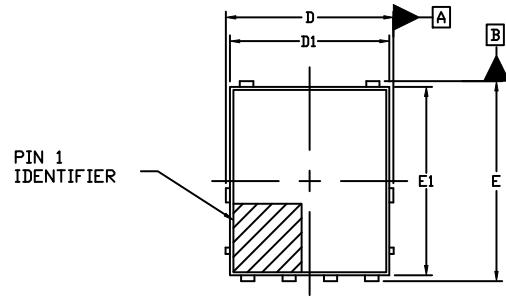
PACKAGE DIMENSIONS

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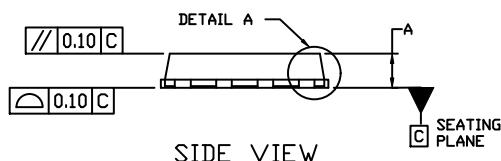


DFNW5 5x6
CASE 507BE
ISSUE O

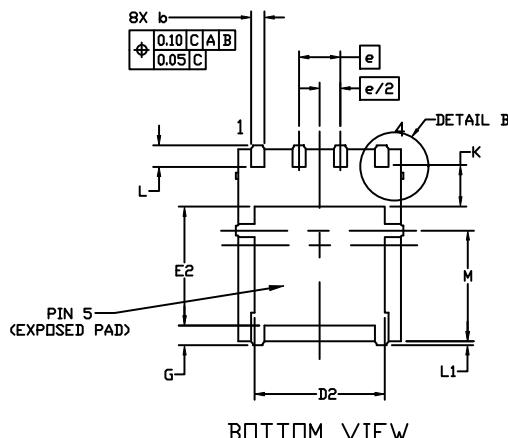
DATE 23 APR 2021



TOP VIEW

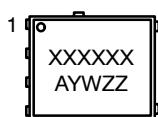


SIDE VIEW



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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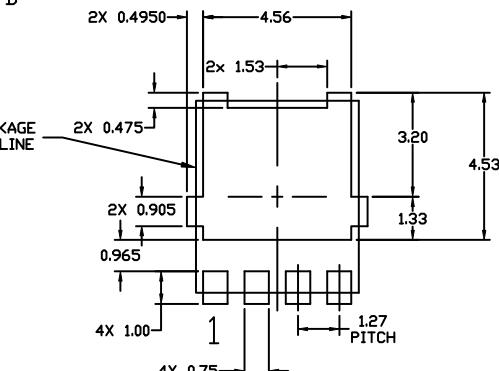
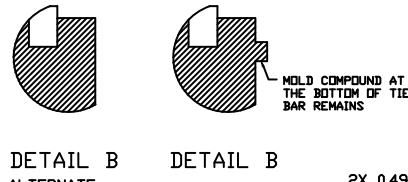
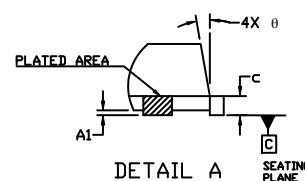
DESCRIPTION: DFNW5 5x6

PAGE 1 OF 1

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27	BSC	
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150	REF	
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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